

32 k × 8 NONVOLATILE SRAM (5 V, 3.3 V)

FEATURES

- Data Retention for at least 10 Years Without Power
- Automatic Write-Protection During Power-up/Power-down Cycles
- Conventional SRAM Operation, Including Unlimited Write Cycles
- Internal Isolation of Battery before Power Application
- 5-V or 3.3-V Operation
- Industry Standard 28-Pin DIP Pinout

GENERAL DESCRIPTION

The CMOS bq4011/Y/LY is a nonvolatile 262,144-bit static RAM organized as 32,768 words by 8 bits. The integral control circuitry and lithium energy source provide reliable nonvolatility coupled with the unlimited write cycles of standard SRAM.

The control circuitry constantly monitors the single supply for an out-of-tolerance condition. When V_{CC} falls out of tolerance, the SRAM is unconditionally write-protected to prevent an inadvertent write operation.

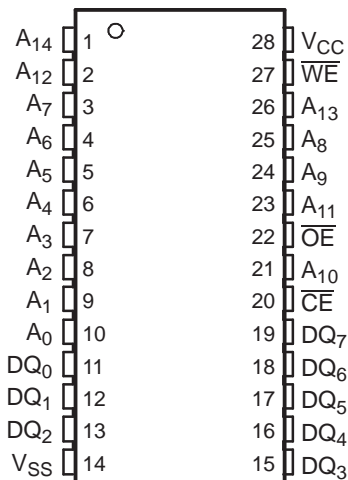
At this time the integral energy source is switched on to sustain the memory until after V_{CC} returns valid.

The bq4011/Y/LY uses extremely low standby current CMOS SRAMs, coupled with small lithium coin cells to provide nonvolatility without long write-cycle times and the write-cycle limitations associated with EEPROM.

The bq4011/Y/LY requires no external circuitry and is compatible with the industry-standard 256-kb SRAM pinout.

PIN CONNECTIONS

28-Pin DIP Module
(TOP VIEW)



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

DEVICE INFORMATION

Table 1. TERMINAL FUNCTIONS

TERMINAL		I/O	DESCRIPTION
NAME	NUMBER		
A ₀	10	I	Address inputs
A ₁	9	I	
A ₂	8	I	
A ₃	7	I	
A ₄	6	I	
A ₅	5	I	
A ₆	4	I	
A ₇	3	I	
A ₈	25	I	
A ₉	24	I	
A ₁₀	21	I	
A ₁₁	23	I	
A ₁₂	2	I	
A ₁₃	26	I	
A ₁₄	1	I	
\overline{CE}	20	I	Chip-enable input
DQ ₀	11	I/O	Data input/output
DQ ₁	12	I/O	
DQ ₂	13	I/O	
DQ ₃	15	I/O	
DQ ₄	16	I/O	
DQ ₅	17	I/O	
DQ ₆	18	I/O	
DQ ₇	19	I/O	
\overline{OE}	22	I	Output enable input
V _{CC}	28	I	Supply voltage input
V _{SS}	14	-	Ground
\overline{WE}	27	I	Write enable input

FUNCTIONAL DESCRIPTION

When power is valid, the bq4011/Y/LY operates as a standard CMOS SRAM. During power-down and power-up cycles, the bq4011/Y/LY acts as a nonvolatile memory, automatically protecting and preserving the memory contents.

Power-down/power-up control circuitry constantly monitors the V_{CC} supply for a power-fail-detect threshold V_{PFD}. The bq4011 monitors for V_{PFD} = 4.62 V typical for use in 5-V systems with 5% supply tolerance. The bq4011Y monitors for V_{PFD} = 4.37 V typical for use in 5-V systems with 10% supply tolerance. The bq4011LY monitors for V_{PFD} = 2.90 V (typ) for use in 3.3-V systems.

When V_{CC} falls below the V_{PFD} threshold, the SRAM automatically write-protects the data. All outputs become high impedance, and all inputs are treated as *don't care*. If a valid access is in process at the time of power-fail detection, the memory cycle continues to completion. If the memory cycle fails to terminate within time t_{WPT}, write-protection takes place.

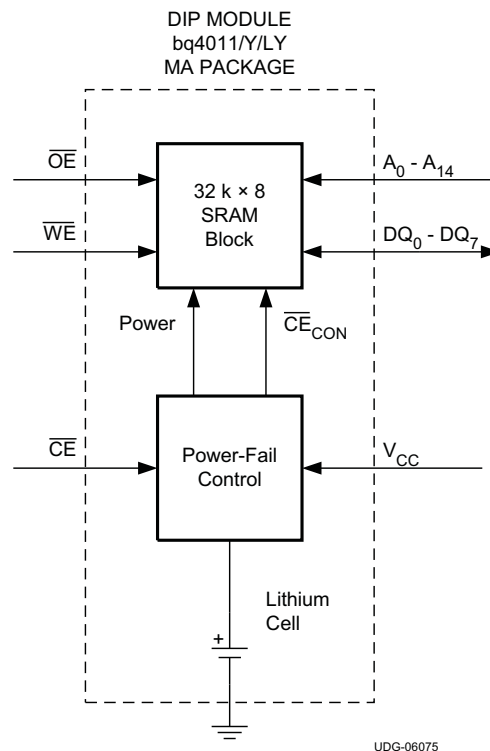
As V_{CC} falls past V_{PFD} and approaches V_{SO}, the control circuitry switches to the internal lithium backup supply, which provides data retention until valid V_{CC} is applied.

When V_{CC} returns to a level above the internal backup cell voltage, the supply is switched back to V_{CC} . After V_{CC} ramps above the V_{PFD} threshold, write-protection continues for a time t_{CER} (120 ms maximum in 5-V system, 85 ms maximum in 3.3-V system) to allow for processor stabilization. Normal memory operation may resume after this time.

The internal coin cells used by the bq4011/Y/LY have an extremely long shelf life and provide data retention for more than 10 years in the absence of system power.

As shipped from TI, the integral lithium cells of the MT-type module are electrically isolated from the memory. (Self-discharge in this condition is approximately 0.5% per year.) Following the first application of V_{CC} , this isolation is broken, and the lithium backup provides data retention on subsequent power-downs.

BLOCK DIAGRAM



TRUTH TABLE

MODE	\overline{CE}	\overline{WE}	\overline{OE}	I/O OPERATION	POWER
Not selected	H	X	X	High-Z	Standby
Output disable	L	H	H	High-Z	Active
Read	L	H	L	D_{OUT}	Active
Write	L	L	X	D_{IN}	Active

ORDERING INFORMATION

For the most current package and ordering information, see the Package Option Addendum at the end of the datasheet, or see the TI website at www.ti.com.

SELECTION GUIDE

DEVICE NUMBER	MAXIMUM ACCESS TIME (ns)	NEGATIVE SUPPLY TOLERANCE (%)	NOMINAL INPUT VOLTAGE V_{CC} (V)	TEMPERATURE (°C)
bq4011MA-70	70	-5	5	0 to 70
bq4011MA-150	150			
bq4011MA-200	200			
bq4011YMA-70	70	-10		
bq4011YMA-100	100			
bq4011YMA-150	150			
bq4011YMA-200	200			
bq4011YMA-70N	70			
bq4011YMA-150N	150	-40 to 85		
bq4011LYMA-70N	70			
			3.3	

PART NUMBERING

PRODUCT LINE	MEMORY DENSITY	INPUT VOLTAGE (V)	NEGATIVE SUPPLY TOLERANCE (%)	PACKAGE	SPEED (ns)	TEMPERATURE °C
bq40	11	L	Y	MA	70	N
	10 = 8 k × 8 11 = 32 k × 8 13 = 128 k × 8 14 = 256 k × 8 15 = 512 k × 8 16 = 1024 k × 8 17 = 2048 k × 8	Blank = 5 L = 3.3	Blank = 5% Y = 10%	MA = DIP	70 85 100 120 150 200	Blank = Commercial (0 to 70) N = Industrial (-40 to 85)

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

PARAMETER		CONDITION	VALUE	UNIT	
V _{CC}	DC voltage applied on VCC relative to VSS		bq4011Y	–0.3 to 7.0	V
			bq4011	–0.3 to 7.0	
			bq4011LY	–0.3 to 6.0	
V _T	DC voltage applied on any pin excluding VCC relative to VSS	V _{VT} ≤ V _{CC} + 0.3 V	bq4011Y	–0.3 to 7.0	V
			bq4011	–0.3 to 7.0	
			bq4011LY	–0.3 to (V _{CC} + 0.3)	
T _{OPR}	Operating temperature	Commercial	0 to 70	°C	
		Industrial	–40 to 85		
T _{STG}	Storage temperature	Commercial	–10 to 70		
		Industrial	–40 to 85		
T _{BIAS}	Temperature under bias	Commercial	–10 to 70		
		Industrial	–40 to 85		
T _{SOLDER}	Soldering temperature	For 10 seconds	260		

(1) Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (T_A = T_{OPR})

		MIN	TYP ⁽¹⁾	MAX	UNIT	
V _{CC}	Supply voltage	bq4011Y	4.50	5.00	5.50	V
		bq4011	4.75	5.00	5.50	
		bq4011LY	3.00	3.30	3.60	
V _{SS}	Supply voltage	0	0	0		
V _{IL}	Low-level input voltage	–0.3		0.8		
V _{IH}	High-level Input voltage	2.2		V _{CC} + 0.3		

(1) Typical values indicate operation at T_A = 25°C.

DC ELECTRICAL CHARACTERISTICS

T_A = T_{OPR}; V_{CC(min)} ≤ V_{CC} ≤ V_{CC(max)}

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I _{LI}	Input leakage current	V _{IN} = V _{SS} to V _{CC}			±1	μA
I _{LO}	Output leakage current	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$			±1	
V _{OH}	Output high voltage	I _{OH} = –1.0 mA	2.4			V
V _{OL}	Output low voltage	I _{OL} = 2.1 mA			0.4	
I _{SB1}	Standby supply current	$\overline{CE} = V_{IH}$		1	2	μA
I _{SB2}	Standby supply current	$\overline{CE} \geq V_{CC} - 0.2$ V, 0V ≤ V _{IN} ≤ 0.2 V, or V _{IN} ≥ V _{CC} – 0.2		0.1	1	mA
I _{CC}	Operating supply current	bq4011			50	mA
		bq4011Y	Minimum cycle, duty = 100%, $\overline{CE} = V_{IL}$, I _{I/O} = 0 mA			
		bq4011LY			30	
V _{PFD}	Power-fail-detect voltage	bq4011	4.55	4.62	4.75	V
		bq4011Y	4.30	4.37	4.50	
		bq4011LY	2.85	2.90	2.95	
V _{SO}	Supply switch-over voltage	bq4011		3		V
		bq4011Y		3		
		bq4011LY		2.9		

(1) Typical values indicate operation at T_A = 25°C, V_{CC} = 5.0 V or V_{CC} = 3.3 V.

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CAPACITANCE ($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{CC} = 5.0\text{ V}$ or $V_{CC} = 3.3\text{ V}$)

PARAMETER ⁽¹⁾		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$C_{I/O}$	Input/output capacitance	Output voltage = 0 V			8	pF
C_{IN}	Input capacitance	Input voltage = 0 V			10	

(1) Ensured by design. Not production tested.

AC TEST CONDITIONS

PARAMETER	TEST CONDITIONS	
	5 V	3.3 V
Input pulse levels	0 V to 3.0 V	0 V to V_{CC}
Input rise and fall times	5 ns	5 ns
Input and output timing reference levels	1.5 V (unless otherwise specified)	50 %
Output load (including scope and jig)	See Figure 1 and Figure 2	See Figure 3 and Figure 4

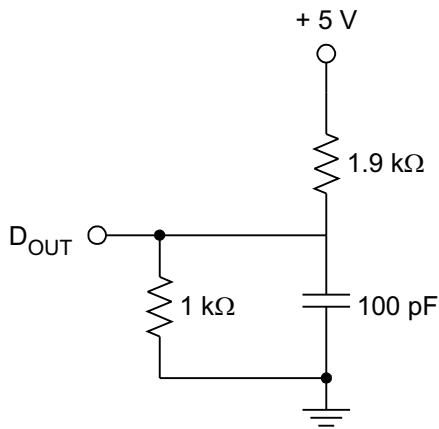


Figure 1. 5-V Output Load A

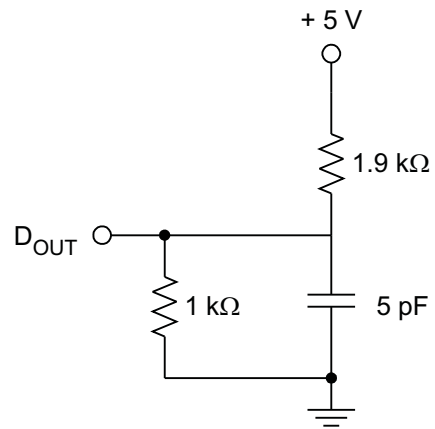


Figure 2. 5-V Output Load B

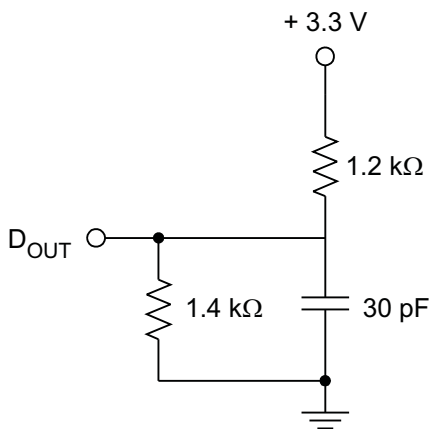


Figure 3. 3.3-V Output Load A

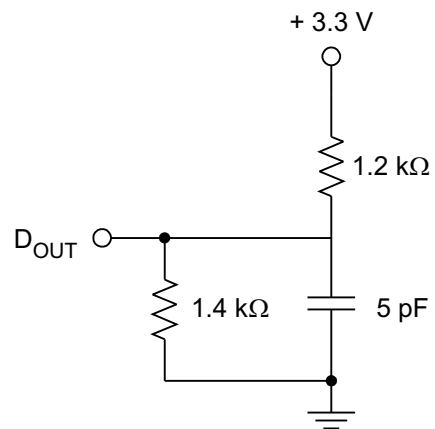
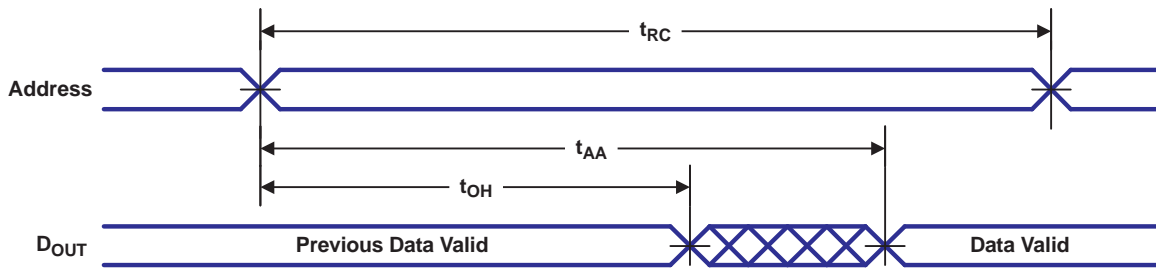


Figure 4. 3.3-V Output Load B

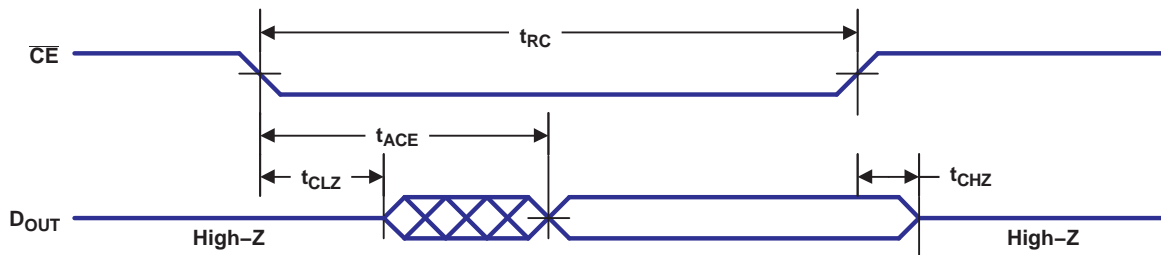
Table 2. READ CYCLE ($T_A = T_{OPR}$, $V_{CC(min)} \leq V_{CC} \leq V_{CC(max)}$)

PARAMETER		TEST CONDITIONS	-70		-100		-150		-200		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{RC}	Read cycle time		70		100		150		200		ns
t_{AA}	Address access time			70		100		150		200	
t_{ACE}	Chip enable access time	Output load A		70		100		150		200	
t_{OE}	Output enable to output valid			35		50		70		90	
t_{CLZ}	Chip enable to output in low Z		5		5		5		5		
t_{OLZ}	Output enable to output in low Z	Output load B	0		0		0		0		
t_{CHZ}	Chip disable to output in high Z		0	25	0	25	0	25	0	25	
t_{OHZ}	Output disable to output in high Z		0	25	0	25	0	25	0	25	
t_{OH}	Output hold from address change	Output load A	10		10		10		10		



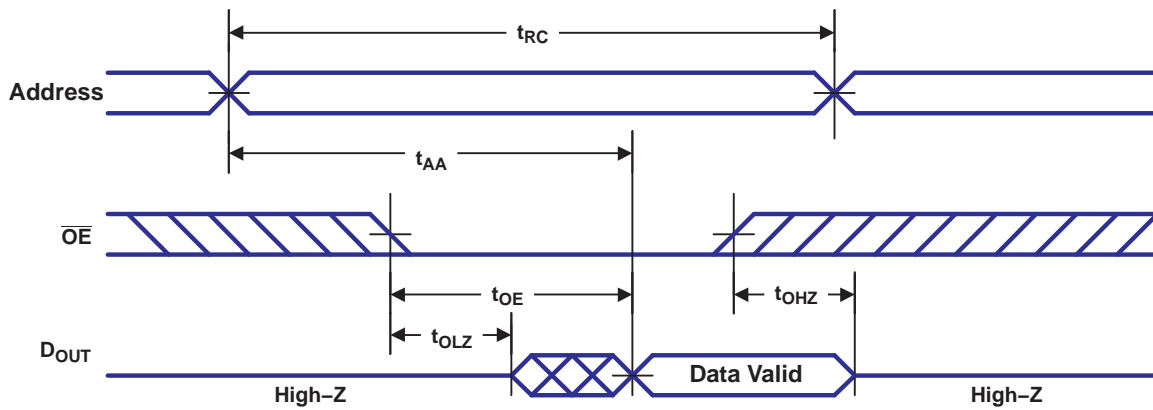
- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = \overline{OE} = V_{IL}$.

Figure 5. Read Cycle No. 1 (Address Access) ⁽¹⁾⁽²⁾



- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = \overline{OE} = V_{IL}$.
- (3) Address is valid prior to or coincident with \overline{CE} transition low.

Figure 6. Read Cycle No. 2 (\overline{CE} Access) ⁽¹⁾⁽²⁾⁽³⁾



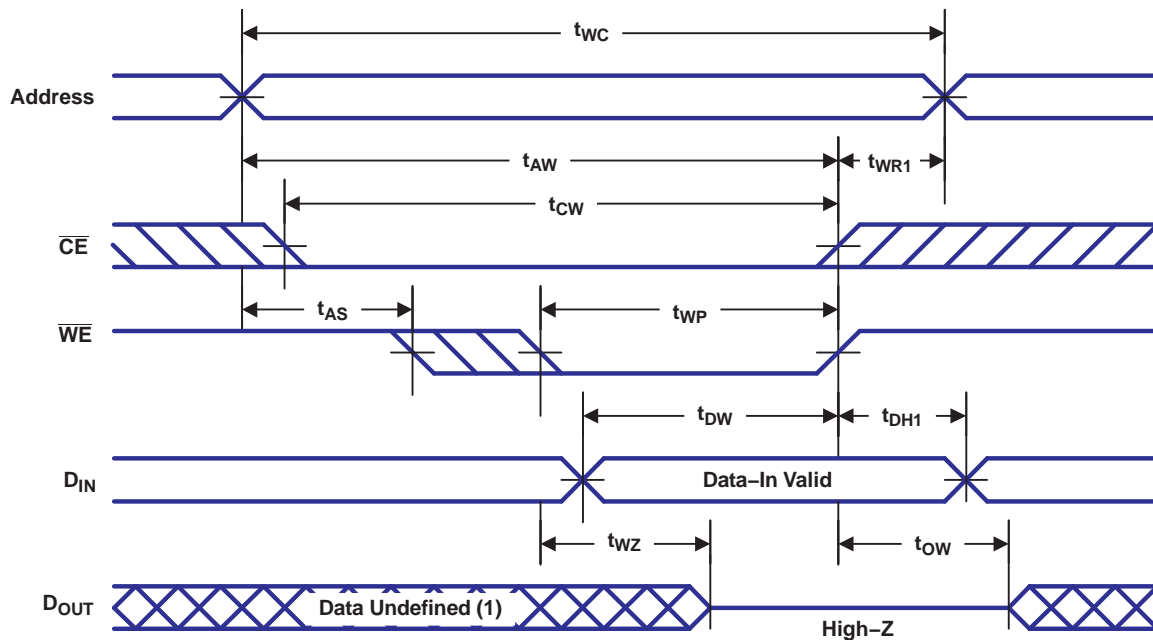
- (1) \overline{WE} is held high for a read cycle.
- (2) Device is continuously selected: $\overline{CE} = V_{IL}$.

Figure 7. Read Cycle No. 3 (\overline{OE} Access) ⁽¹⁾⁽²⁾

Table 3. WRITE CYCLE ($T_A = T_{OPR}$, $V_{CC(min)} \leq V_{CC} \leq V_{CC(max)}$)

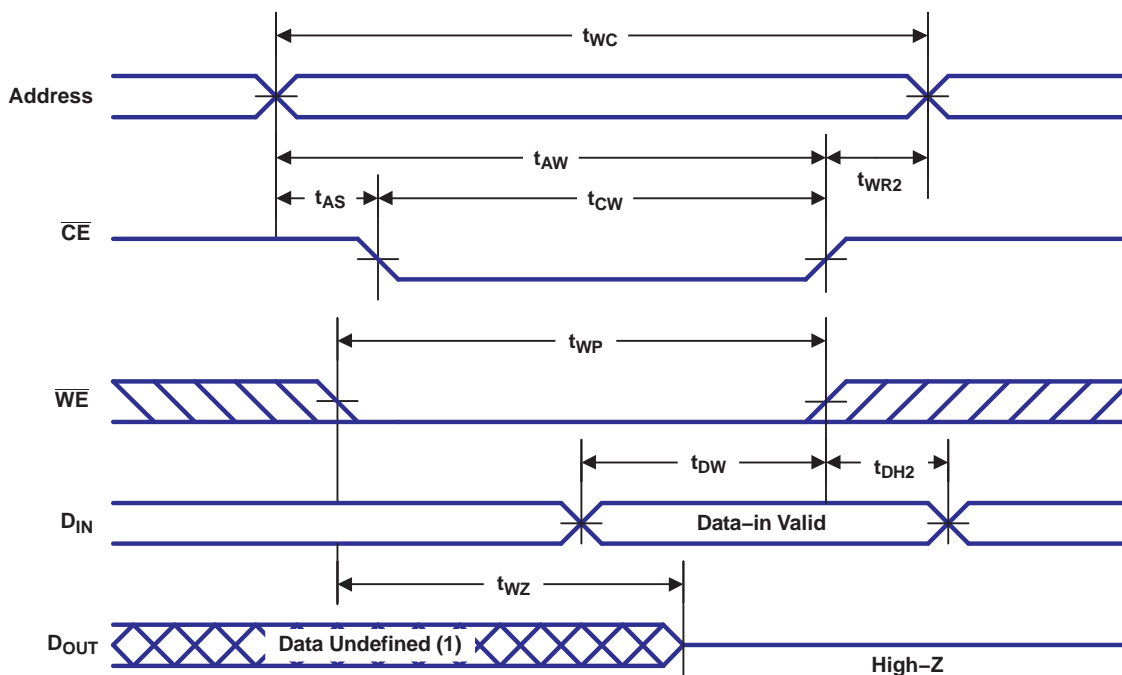
PARAMETER	TEST CONDITIONS	-70		-100		-150		-200		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{WC}	Write cycle time	70		100		150		200		ns
t_{CW}	Chip enable to end of write	65		90		100		150		
t_{AW}	Address valid to end of write	65		80		90		150		
t_{AS}	Address setup time	0		0		0		0		
t_{WP}	Write pulse width	55		75		90		130		
t_{WR1}	Write recovery time (write cycle 1)	5		5		5		5		
t_{WR2}	Write recovery time (write cycle 2)	15		15		15		15		
t_{DW}	Data valid to end of write	30		40		50		70		
t_{DH1}	Data hold time (write cycle 1)	0		0		0		0		
t_{DH2}	Data hold time (write cycle 2)	0		0		0		0		
t_{WZ}	Write enabled to output in high Z	0	25	0	30	0	50	0	70	
t_{OW}	Output active from end of write	5		5		5		5		

- (1) A write ends at the earlier transition of \overline{CE} going high and \overline{WE} going high.
- (2) A write occurs during the overlap of a low \overline{CE} and a low \overline{WE} . A write begins at the later transition of \overline{CE} going low and \overline{WE} going low.
- (3) Either t_{WR1} or t_{WR2} must be met.
- (4) Either t_{DH1} or t_{DH2} must be met.
- (5) If \overline{CE} goes low simultaneously with \overline{WE} going low or after \overline{WE} going low, the outputs remain in high-impedance state.



- (1) \overline{CE} or \overline{WE} must be high during address transition.
- (2) Because I/O may be active (\overline{OE} low) during this period, data input signals of opposite polarity to the outputs must not be applied.
- (3) If \overline{OE} is high, the I/O pins remain in a state of high impedance.

Figure 8. Write Cycle No. 1 (\overline{WE} -Controlled) (1)(2)(3)



- (1) \overline{CE} or \overline{WE} must be high during address transition.
- (2) Because I/O may be active (\overline{OE} low) during this period, data input signals of opposite polarity to the outputs must not be applied.
- (3) If \overline{OE} is high, the I/O pins remain in a state of high impedance.
- (4) Either t_{WR1} or t_{WR2} must be met.
- (5) Either t_{DH1} or t_{DH2} must be met.

Figure 9. Write Cycle No. 2 (\overline{CE} -Controlled) (1)(2)(3)(4)(5)

Table 4. 5-V POWER-DOWN/POWER-UP ($T_A = T_{OPR}$)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_{PF}	V_{CC} slew, 4.75 to 4.25 V		300			μ s
t_{FS}	V_{CC} slew, 4.25 to V_{SO}		10			μ s
t_{PU}	V_{CC} slew, V_{SO} to V_{PFD} (max.)		0			μ s
t_{CER}	Chip enable recovery time	Time during which SRAM is write-protected after V_{CC} passes V_{PFD} on power-up.	40	80	120	ms
t_{DR}	Data-retention time in absence of V_{CC}	$T_A = 25^\circ\text{C}$ ⁽²⁾	10			years
t_{WPT}	Write-protect time	Delay after V_{CC} slews down past V_{PFD} before SRAM is writeprotected.	40	100	150	μ s

- (1) Typical values indicate operation at $T_A = 25^\circ\text{C}$, $V_{CC} = 5\text{V}$.
 (2) Batteries are disconnected from circuit until after V_{CC} is applied for the first time. t_{DR} is the accumulated time in absence of power beginning when power is first applied to the device.

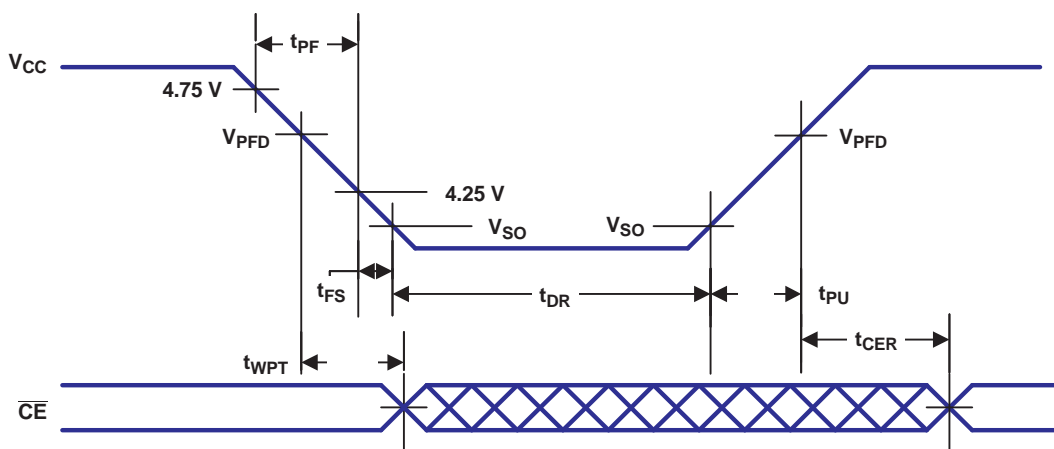


Figure 10. 5-V Power-Down/Power-Up Timing

Table 5. 3.3-V POWER-DOWN/POWER-UP ($T_A = T_{OPR}$)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
t_F	V_{CC} slew, 3 V to 0 V		300			μ s
t_R	V_{CC} slew, V_{SO} to $V_{PFD(max)}$		100			
t_{CER}	Chip enable recovery time	Time during which SRAM is write-protected after V_{CC} passes V_{PFD} on power-up.	10		85	ms
t_{DR}	Data-retention time in absence of V_{CC}	$T_A = 25^\circ\text{C}^{(2)}$	10			years

- (1) Typical values indicate operation at $T_A = 25^\circ\text{C}$, $V_{CC} = 3.3$ V.
- (2) Batteries are disconnected from circuit until after V_{CC} is applied for the first time. Data retention time (t_{DR}) is the accumulated time in absence of power beginning when power is first applied to the device.

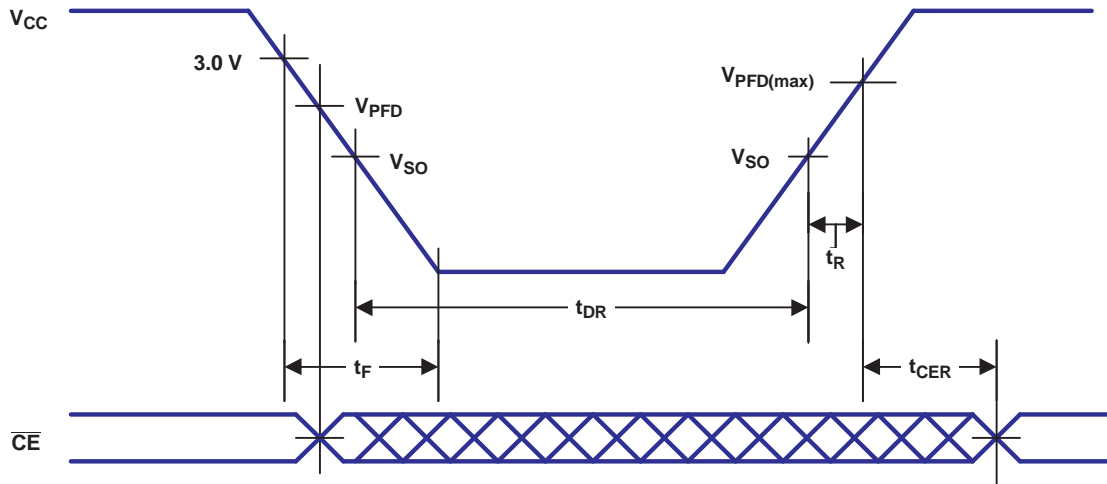


Figure 11. 3.3-V Power-Down/Power-Up Timing

CAUTION:

Negative undershoots below the absolute maximum rating of -0.3 V in battery-backup mode may affect data integrity.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ4011LYMA-70N	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	-40 to 85		
BQ4011MA-100	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011MA-150	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011YMA-100	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011YMA-150	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011YMA-200	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011YMA-70	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	0 to 70		
BQ4011YMA-70N	OBSOLETE	DIP MODULE	MA	28		TBD	Call TI	Call TI	-40 to 85		

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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